TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

# 16DL2C41A

## SWITCHING TYPE POWER SUPPLY APPLICATION

#### **CONVERTER & CHOPPER APPLICATION**

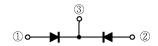
• Repetitive Peak Reverse Voltage : V<sub>RRM</sub>=200V

• Average Output Rectified Current : IO=16A

Ultra Fast Reverse-Recovery Time : t<sub>rr</sub>=35ns (Max.)
 Low Forward Voltage : V<sub>FM</sub>=0.98V (Max.)

Low Switching Losses and Output Noise.

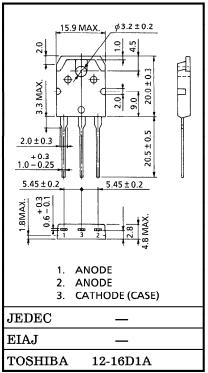
#### **POLARITY**



## **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Reverse Voltage	$v_{RRM}$	200	V	
Average Output Rectified Current (Full Sine Waveform)	IO	16	A	
Peak One Cycle Surge Forward	Trans	80 (50Hz)	A	
Current (Non-Repetitive)	IFSM	88 (60Hz)		
Junction Temperature	$\mathbf{T_{j}}$	-40~150	$^{\circ}\mathrm{C}$	
Storage Temperature Range	$T_{ m stg}$	-40~150	°C	

#### Unit in mm



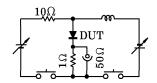
Weight: 4.85g

### ELECTRICAL CHARACTERISTICS (Ta = 25°C) (Note 1)

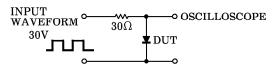
		, ,			
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Peak Forward Voltage	$V_{ extbf{FM}}$	I <sub>FM</sub> =8A	_	0.98	V
Repetitive Peak Reverse Current	$I_{RRM}$	V <sub>RRM</sub> =Rated	_	50	$\mu$ A
Reverse Recovery Time	t <sub>rr</sub>	$I_F = 2.0A$ di/dt=-50A/ $\mu$ s (Note 2)	_	35	ns
Forward Recovery Time	tfr	I <sub>F</sub> =1.0A (Note 3)	_	100	ns
Thermal Resistance	$R_{ ext{th }(j-c)}$	DC Total, Junction to Case	_	1.9	°C/W

Note 1: A value of one cell.

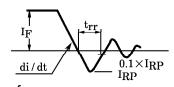
Note 2: trr TEST CIRCUIT



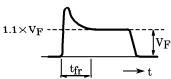
Note 3: tfr TEST CIRCUIT



t<sub>rr</sub> Waveform

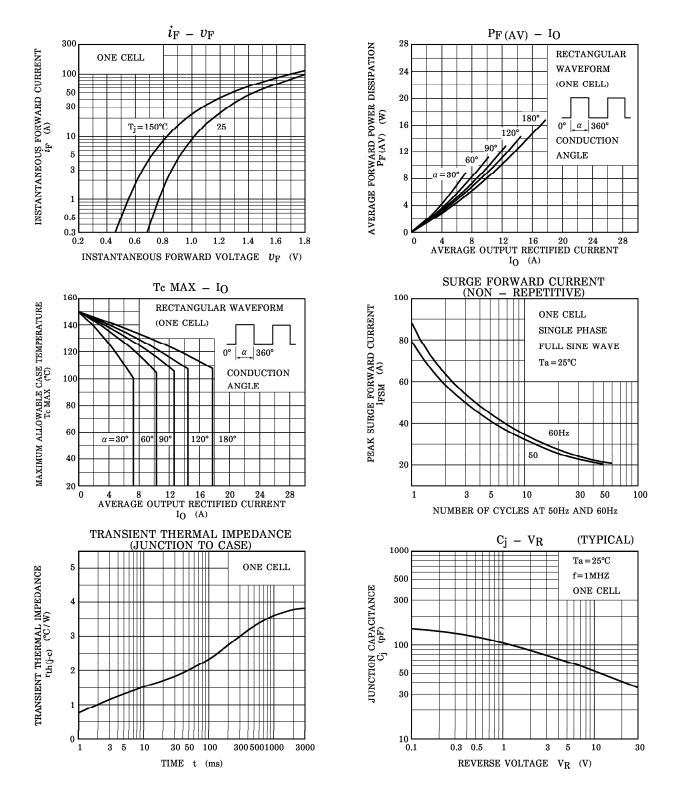


tfr Waveform



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